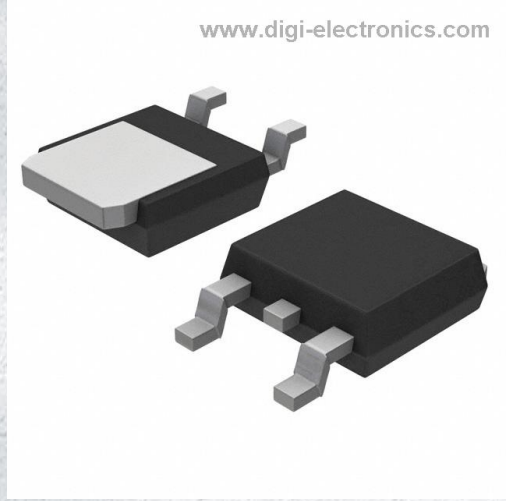
MJD50G Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number	MJD50G-DG
Manufacturer	onsemi
Manufacturer Product Number	MJD50G
Description	TRANS NPN 400V 1A DPAK
Detailed Description	Bipolar (BJT) Transistor NPN 400 V 1 A 10MHz 1.56 W Surface Mount DPAK

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
MJD50G	onsemi
Series:	Product Status:
-	Active
Transistor Type:	Current - Collector (Ic) (Max):
NPN	1 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ Ib, Ic:
400 V	1V @ 200mA, 1A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
200µA	30 @ 300mA, 10V
Power - Max:	Frequency - Transition:
1.56 W	10MHz
Operating Temperature:	Mounting Type:
-65°C ~ 150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
TO-252-3, DPAK (2 Leads + Tab), SC-63	DPAK
Base Product Number:	
MJD50	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

DATA SHEET
www.onsemi.com

High Voltage Power Transistors

DPAK for Surface Mount Applications

MJD47, NJVMJD47T4G, MJD50, NJVMJD50T4G

Designed for line operated audio output amplifier, switchmode supply drivers and other switching applications.

Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Electrically Similar to Popular TIP47, and TIP50
- Epoxy Meets UL 94 V−0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free and are RoHS Compliant

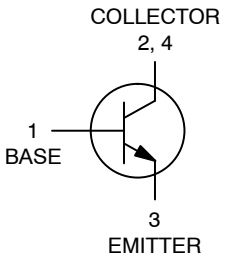
MAXIMUM RATINGS

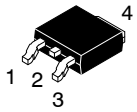
Rating	Symbol	Max	Unit
Collector−Emitter Voltage MJD47, NJVMJD47T4G MJD50, NJVMJD50T4G	V_{CEO}	 250 400	Vdc
Collector−Base Voltage MJD47, NJVMJD47T4G MJD50, NJVMJD50T4G	V_{CB}	 350 500	Vdc
Emitter−Base Voltage	V_{EB}	5	Vdc
Collector Current − Continuous	I_C	1	Adc
Collector Current − Peak	I_{CM}	2	Adc
Base Current	I_B	0.6	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	 15 0.12	 W W/°C
Total Power Dissipation (Note 1) @ T_A = 25°C Derate above 25°C	P_D	 1.56 0.0125	 W W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +150	°C
ESD − Human Body Model	HBM	3B	V
ESD − Machine Model	MM	C	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

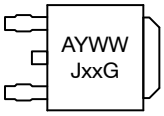
NPN SILICON POWER TRANSISTORS
1 AMPERE
250, 400 VOLTS, 15 WATTS





DPAK
CASE 369C
STYLE 1

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
Jxx = Device Code
xx = 47 or 50
G = Pb−Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MJD47, NJVMJD47T4G, MJD50, NJVMJD50T4G

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction−to−Case	$R_{\theta JC}$	8.33	°C/W
Thermal Resistance Junction−to−Ambient (Note 2)	$R_{\theta JA}$	80	°C/W
Lead Temperature for Soldering Purpose	T_L	260	°C

2. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector−Emitter Sustaining Voltage (Note 3) (I_C = 30 mAdc, I_B = 0) MJD47, NJVMJD47T4G MJD50, NJVMJD50T4G	$V_{CEO(sus)}$	 250 400	 – –	Vdc
Collector Cutoff Current (V_{CE} = 150 Vdc, I_B = 0) MJD47, NJVMJD47T4G (V_{CE} = 300 Vdc, I_B = 0) MJD50, NJVMJD50T4G	I_{CEO}	 – –	 0.2 0.2	mAdc
Collector Cutoff Current (V_{CE} = 350 Vdc, V_{BE} = 0) MJD47, NJVMJD47T4G (V_{CE} = 500 Vdc, V_{BE} = 0) MJD50, NJVMJD50T4G	I_{CES}	 – –	 0.1 0.1	mAdc
Emitter Cutoff Current (V_{BE} = 5 Vdc, I_C = 0)	I_{EBO}	 –	 1	mAdc
ON CHARACTERISTICS (Note 3)				
DC Current Gain (I_C = 0.3 Adc, V_{CE} = 10 Vdc) (I_C = 1 Adc, V_{CE} = 10 Vdc)	h_{FE}	 30 10	 150 –	–
Collector−Emitter Saturation Voltage (I_C = 1 Adc, I_B = 0.2 Adc)	$V_{CE(sat)}$	 –	 1	Vdc
Base−Emitter On Voltage (I_C = 1 Adc, V_{CE} = 10 Vdc)	$V_{BE(on)}$	 –	 1.5	Vdc
DYNAMIC CHARACTERISTICS				
Current Gain − Bandwidth Product (I_C = 0.2 Adc, V_{CE} = 10 Vdc, f = 2 MHz)	f_T	 10	 –	MHz
Small−Signal Current Gain (I_C = 0.2 Adc, V_{CE} = 10 Vdc, f = 1 kHz)	h_{fe}	 25	 –	–

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

MJD47, NJVMJD47T4G, MJD50, NJVMJD50T4G

TYPICAL CHARACTERISTICS

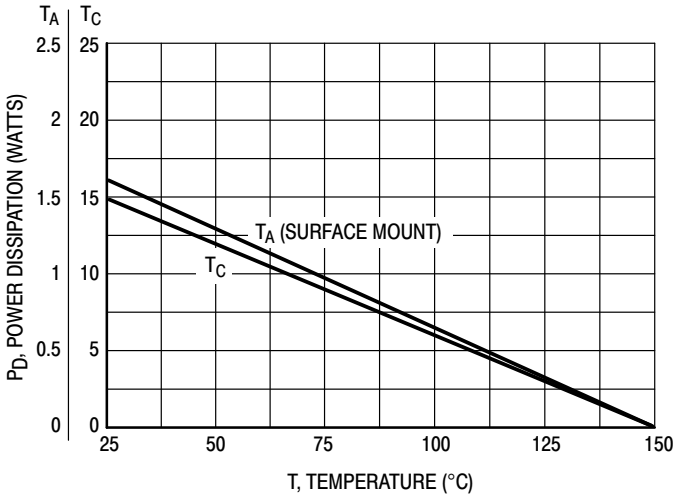


Figure 1. Power Derating

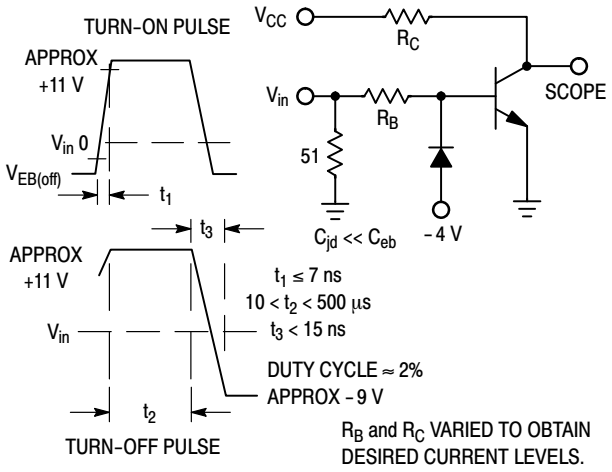


Figure 2. Switching Time Equivalent Circuit

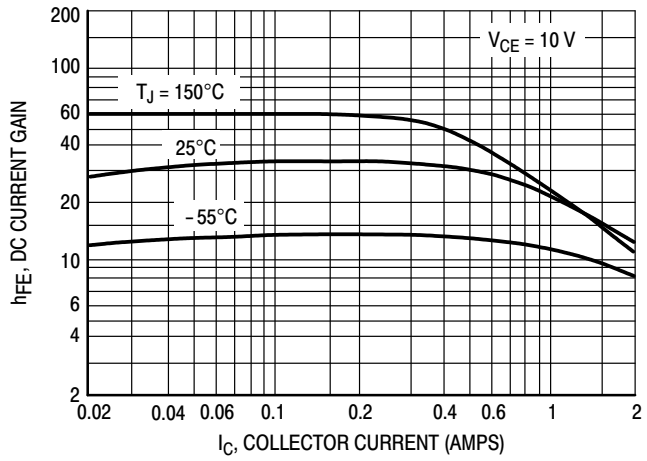


Figure 3. DC Current Gain

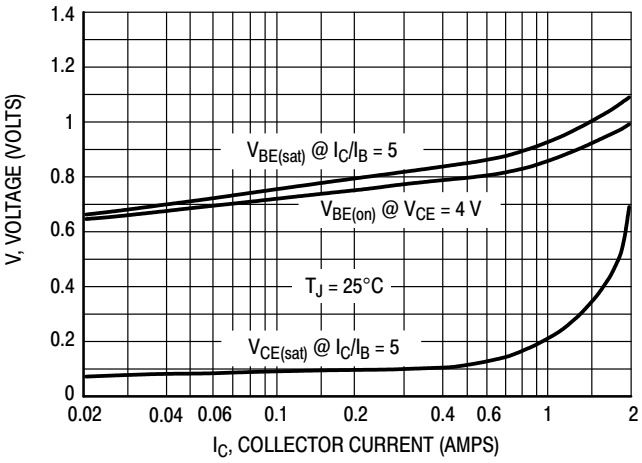


Figure 4. "On" Voltages

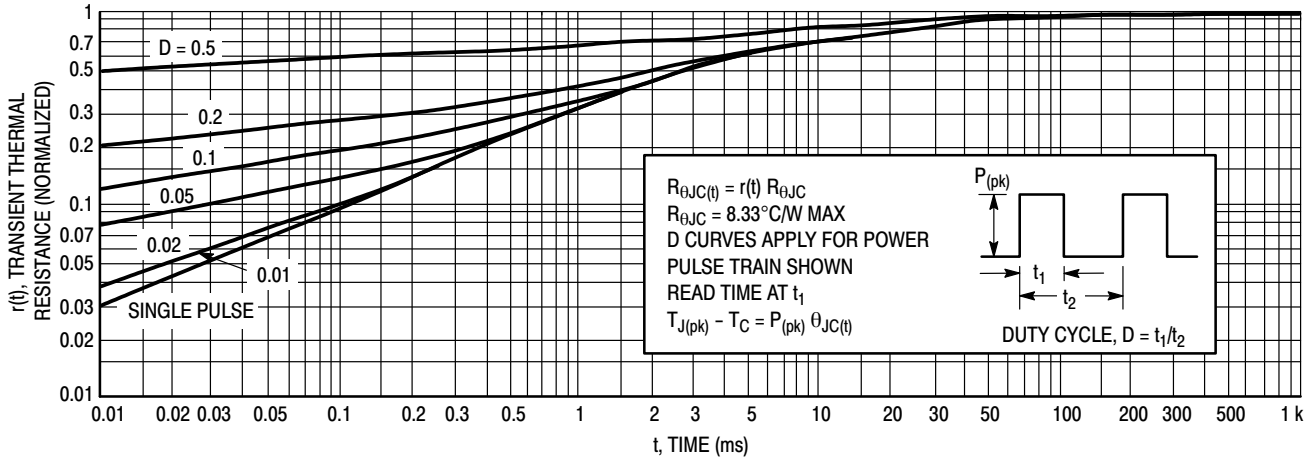


Figure 5. Thermal Response

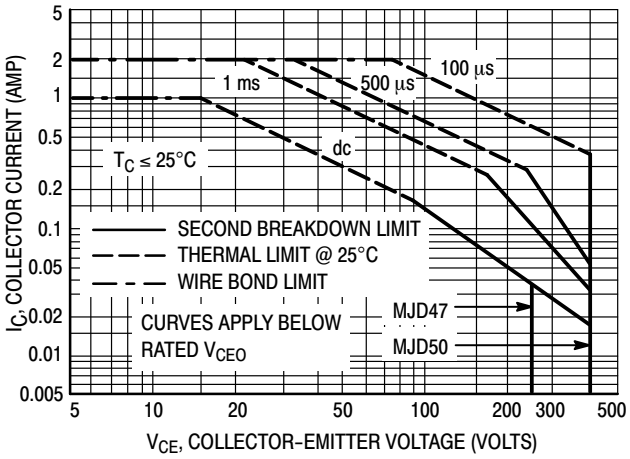


Figure 6. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on $T_{J(pk)} = 150°C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150°C$. $T_{J(pk)}$ may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

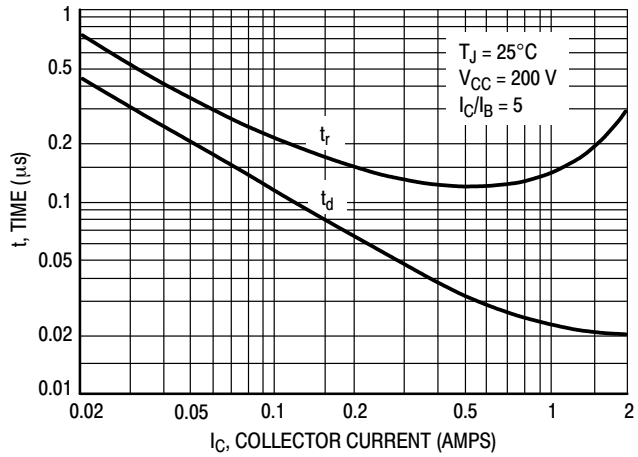


Figure 7. Turn−On Time

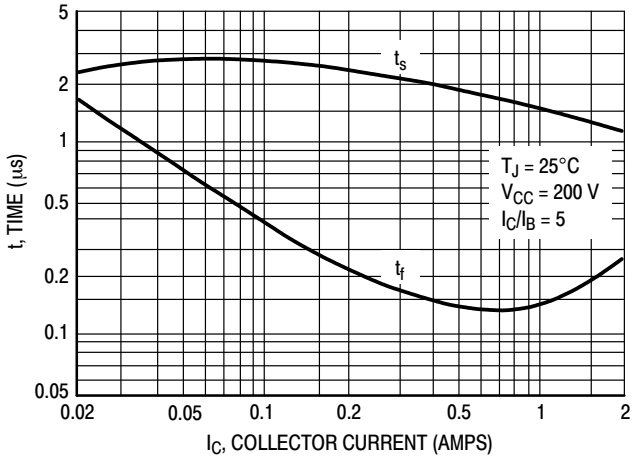


Figure 8. Turn-Off Time

MJD47, NJVMJD47T4G, MJD50, NJVMJD50T4G

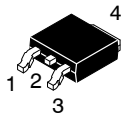
ORDERING INFORMATION

Device	Package	Shipping†
MJD47G	369C (Pb−Free)	75 Units / Rail
MJD47T4G	369C (Pb−Free)	2,500 / Tape & Reel
NJVMJD47T4G*	369C (Pb−Free)	2,500 / Tape & Reel
MJD50G	369C (Pb−Free)	75 Units / Rail
MJD50T4G	369C (Pb−Free)	2,500 / Tape & Reel
NJVMJD50T4G*	369C (Pb−Free)	2,500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable.

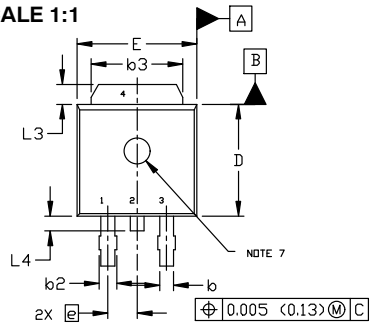
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



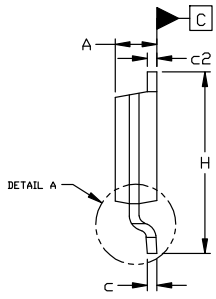
DPAK (SINGLE GAUGE)
CASE 369C
ISSUE G

DATE 31 MAY 2023

SCALE 1:1



TOP VIEW

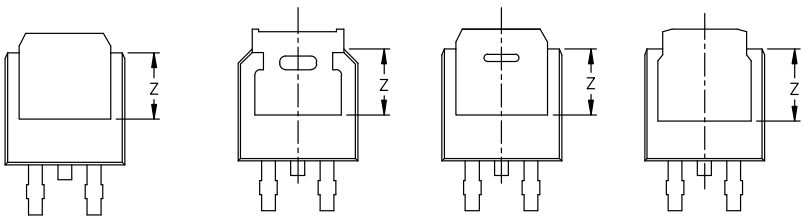


SIDE VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

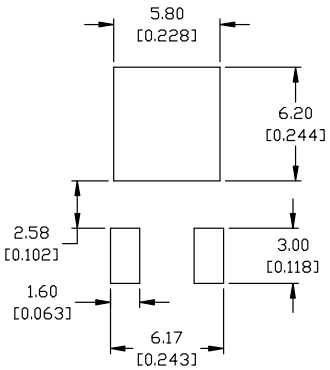
DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114 REF		2.90 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	----	0.040	---	1.01
Z	0.155	----	3.93	---



BOTTOM VIEW

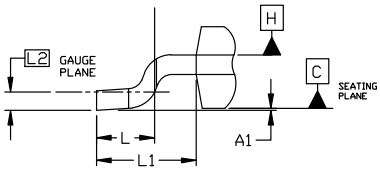
BOTTOM VIEW

ALTERNATE CONSTRUCTIONS



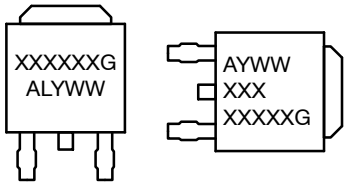
RECOMMENDED MOUNTING FOOTPRINT*

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.



DETAIL A
ROTATED 90° CW

GENERIC MARKING DIAGRAM*



IC **Discrete**

XXXXXX = Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 5:
PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:
PIN 1. MT1
2. MT2
3. GATE
4. MT2

STYLE 7:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 8:
PIN 1. N/C
2. CATHODE
3. ANODE
4. CATHODE

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. RESISTOR ADJUST
4. CATHODE

STYLE 10:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

DOCUMENT NUMBER:	**98AON10527D**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	**DPAK (SINGLE GAUGE)**	**PAGE 1 OF 1**

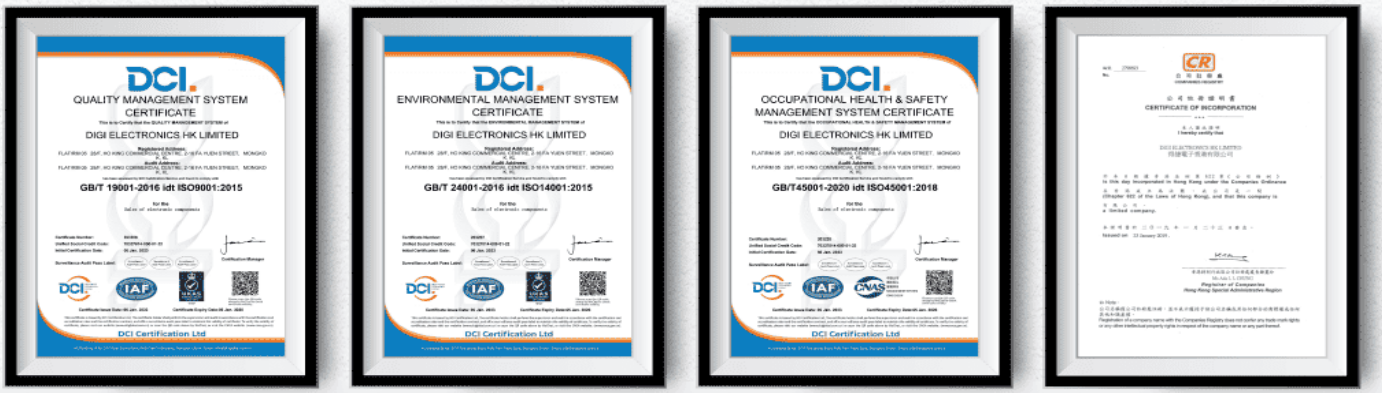
ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales

OUR CERTIFICATE

DiGi provide top-quality products and perfect service for customer worldwide through standardization, technological innovation and continuous improvement. DiGi through third-party certification, we striciy control the quality of products and services. Welcome your RFQ to Email: Info@DiGi-Electronics.com



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.